

LAST - [10508974.wspcl]

S41: (354) (magnetic near flux near concentrator)
S42: (240) S41 and @ad<"20020326"
S43: (33) "4455626"
S44: (904) 257/421-422.ccls.
S45: (386) S44 and @ad<"20020326"
S46: (1) "6555858".PN.
S47: (1) "5734605".PN.
S48: (3829) motoyoshi.in.
S49: (266) Ikarashi.in.
S50: (4089) S48 S49
S51: (49) S50 and (magnetic near memory near device)
S52: (3) S51 and @ad<"20020326"
S53: (294897) Sony.as.
S54: (174) S53 and (magnetic near memory near device)
S55: (37) S54 and @ad<"20020326"
S56: (8026) (magnetic near random near access near memory) MRJ
S57: (1782759) (nonvolatile near magnetic memory)
S59: (45804) FRAM
S60: (6880) TMR (Tunnel near Magneto near Resistance)
S61: (1438) S56 and S60
S62: (1) 10/508924
S63: (45) 365/130.ccls. and (magnetic near flux)
S64: (6) S63 and @ad<"20020326"
S65: (254) 365/171.ccls. and (magnetic near flux)
S66: (82) S65 and @ad<"20020326"

US:PGZUB:USPATRUSOCNROXRODERWENT:BNITDS
Data Provider: OR
S54 and @ad<"20020326"

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	U	1	Document ID	Source	Pages	Title	Current OR	Current XRS	Retrieval C	Inventor	S	C	D	3	2
1			JP 53105122 A	19780913	7	MAGNETIC MEMORY DEVICE				MORIO, MINORU et al.					
2			JP 01194188 A	19890804	5	MAGNETIC MEMORY DEVICE		365/13		NAKADA, SATOSHI et al.					
3			US 4996667 A	19910226	6	Electron beam addressable recording device utilizing	365/117	365/118; 365/145		Murano, Kanji et al.					
4			US 5508940 A	19960416	28	Random access audio/video processor with multiple	715/723	360/13; 715/500.1		Rossmore, David L. et al.					
5			JP 2000198435 A	20000704	9	Magnetic tunneling joining element for magnetic head,									
6			US 6397476 B1	20020514	29	Magnetic functional element and magnetic recording	428/212	428/826; 428/847.5;		Iwasaki, Yoh et al.					
7			JP 2002246568 A	20020830	12	MAGNETIC MEMORY DEVICE AND ITS MANUFACTURING METHOD				IGARASHI, MINORU					
8			JP 2002246566 A	20020830	7	STORAGE MEMORY DEVICE		257/E21.665; 257/E27.005		KANO, HIROSHI et al.					
9			JP 2002246568 A	20020830	12	Magnetic memory device e.g. magnetic random access									
10			JP 2002246566 A	20020830	7	Magnetic memory device has write-in lines provided to									
11			US 20020176277 A	20021128	11	Magnetic memory e.g. magnetic random access				BESSHO, K et al.					
12			JP 2002353418 A	20021206	7	MAGNETORESISTIVE EFFECT ELEMENT AND MAGNETIC MEMORY				MIZUGUCHI, TETSUYA et al.					
13			JP 2002353413 A	20021206	9	MAGNETORESISTIVE EFFECT ELEMENT AND MAGNETIC MEMORY									

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